Electrical Characteristics - MOSFET (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 1)						
Drain-Source Breakdown Voltage	BV_{DSS}	50	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	10	μA	V_{DS} = 50V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	1.0 5.0	μA	V_{GS} = ±8V, V_{DS} = 0V V_{GS} = ±12V, V_{DS} = 0V
ON CHARACTERISTICS (Note 1)						
Gate Threshold Voltage	$V_{GS(th)}$	0.7	0.8	1.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	3.1	4	Ω	V_{GS} = 4V, I_D = 100mA
		—	4	5		V_{GS} = 2.5V, I_D = 80mA
Forward Transconductance	g_{FS}	180	—	—	ms	V_{DS} = 10V, I_D = 100mA, f = 1.0kHz
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	25	—	pF	V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	5	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.1	—	pF	

Electrical Characteristics - NPN Transistor (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	(Note 5)	$V_{(BR)CBO}$	50	—	—	V	I_C = 10μA, I_B = 0
Collector-Emitter Breakdown Voltage	(Note 5)	$V_{(BR)CEO}$	45	—	—	V	I_C = 10mA, I_B = 0
Emitter-Base Breakdown Voltage	(Note 5)	$V_{(BR)EBO}$	6	—	—	V	I_E = 1μA, I_C = 0
DC Current Gain	(Note 5)	h_{FE}	200	290	450	—	V_{CE} = 5.0V, I_C = 2.0mA
Collector-Emitter Saturation Voltage	(Note 5)	$V_{CE(SAT)}$	—	—	100 300	mV	I_C = 10mA, I_B = 0.5mA I_C = 100mA, I_B = 5.0mA
Base-Emitter Saturation Voltage	(Note 5)	$V_{BE(SAT)}$	—	700 900	—	mV	I_C = 10mA, I_B = 0.5mA I_C = 100mA, I_B = 5.0mA
Base-Emitter Voltage	(Note 5)	V_{BE}	580 —	660 —	700 770	mV	V_{CE} = 5.0V, I_C = 2.0mA V_{CE} = 5.0V, I_C = 10mA
Collector Cut-Off Current	(Note 5)	I_{CBO}	—	—	15 5.0	nA μA	V_{CB} = 30V V_{CB} = 30V, T_A = +150°C
Collector-Emitter Cut-Off Current	(Note 5)	I_{CES}	—	—	-100	nA	V_{CE} = -45V
Gain Bandwidth Product		f_T	100	—	—	MHz	V_{CE} = 5.0V, I_C = 10mA, f = 100MHz
Output Capacitance		C_{OBO}	—	—	4.5	pF	V_{CB} = 10V, f = 1.0MHz
Noise Figure		NF	—	—	10	dB	V_{CE} = 5V, R_S = 2.0kΩ, f = 1.0kHz, BW = 200Hz

Note: 5. Short duration pulse test used to minimize self-heating effect.

MOSFET

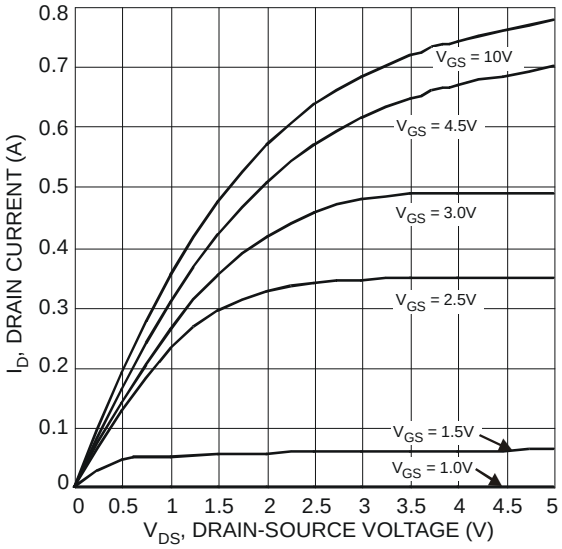


Fig. 1 Typical Output Characteristics

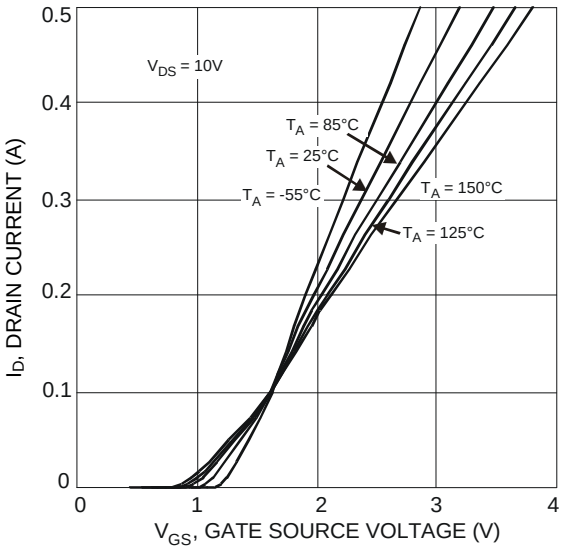


Fig. 2 Typical Transfer Characteristics

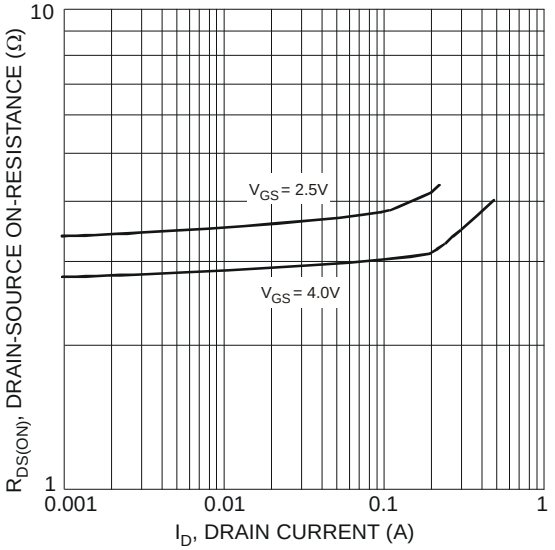


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

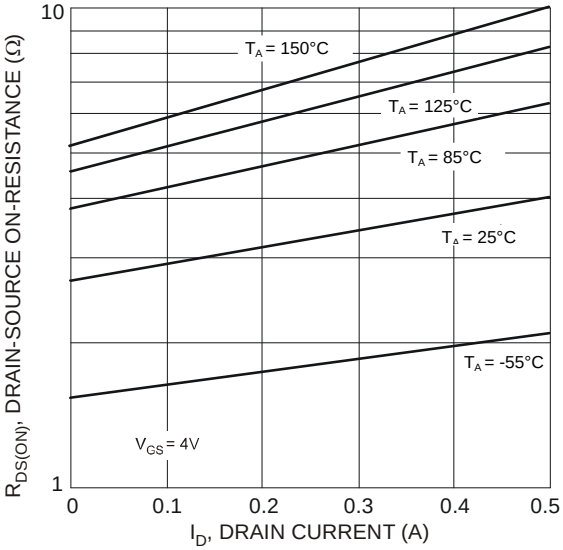


Fig. 4 Typical Drain-Source On-Resistance
vs. Drain Current and Temperature

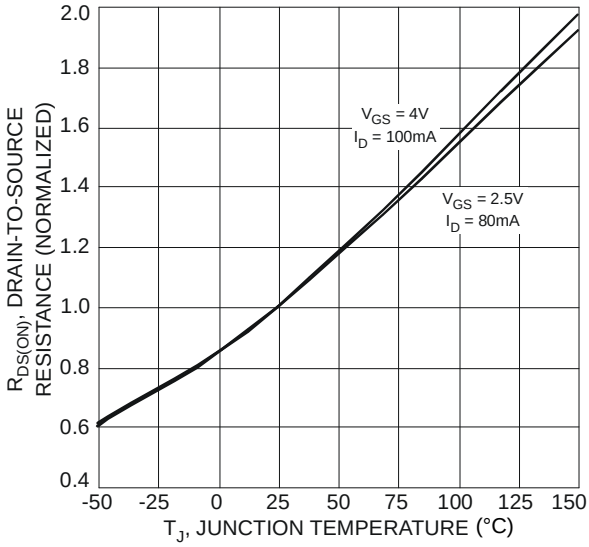


Fig. 5 On-Resistance Variation with Temperature

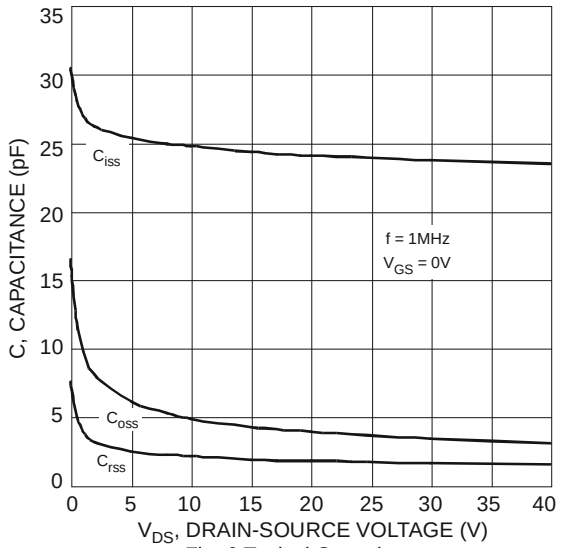


Fig. 6 Typical Capacitance

MOSFET (continued)

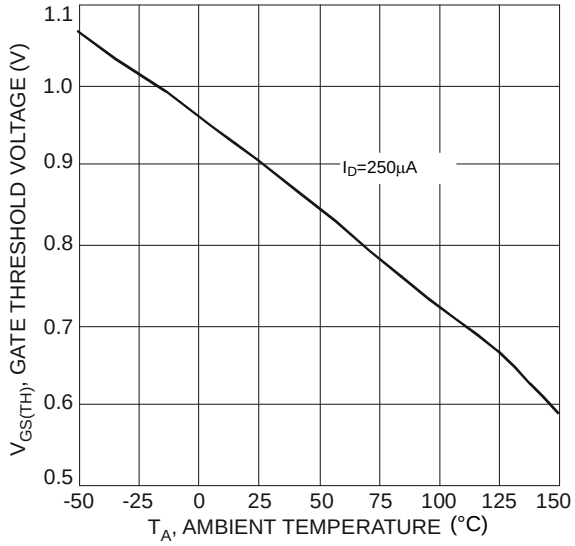


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

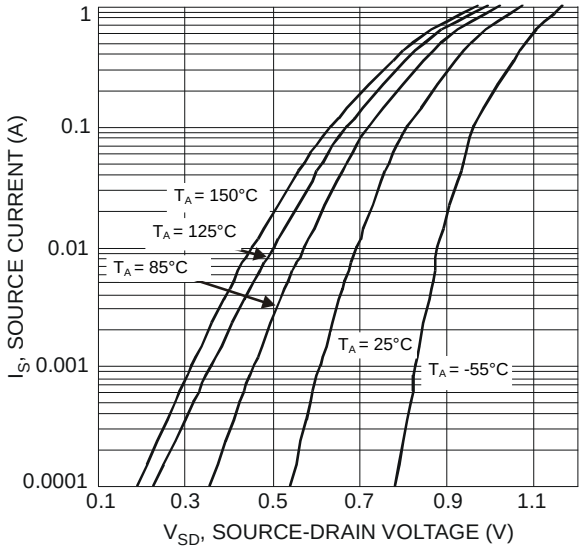


Fig. 8 Diode Forward Voltage vs. Current

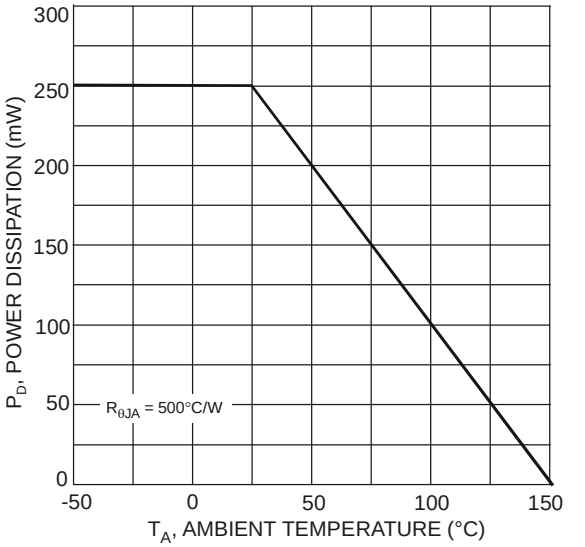


Fig. 9 Derating Curve - Total Package Power Dissipation

NPN Transistor

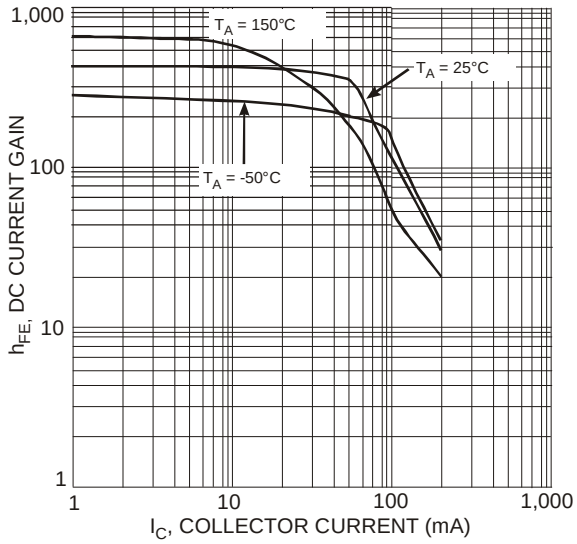


Fig. 10 Typical DC Current Gain vs. Collector Current

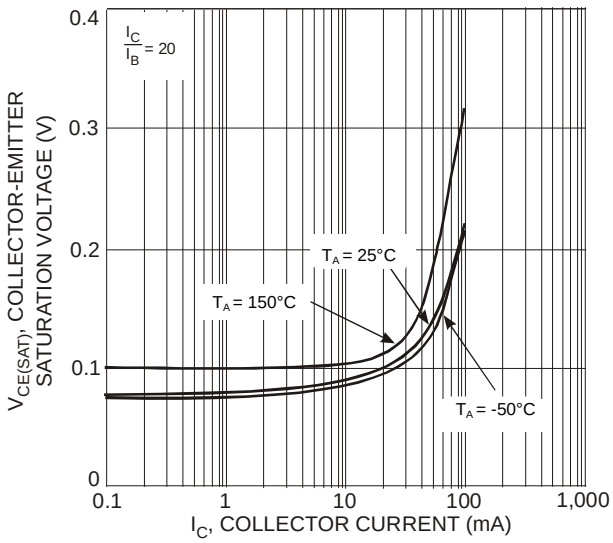


Fig. 11 Typical Collector-Emitter Saturation Voltage vs. Collector Current

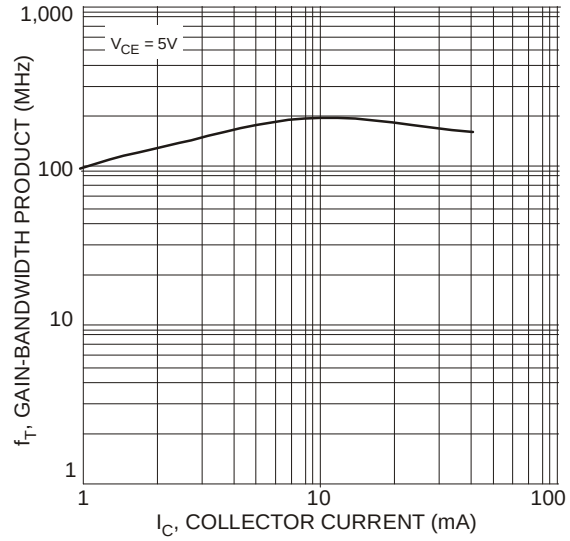


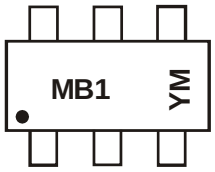
Fig. 12 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 6)

Part Number	Case	Packaging
DMB53D0UDW-7	SOT-363	3000/Tape & Reel

Note: 6. For packaging details, go to our website at https://www.diodes.com/assets/Packaging-Support-Docs/Ap02007.pdf.

Marking Information



MB1 = Marking Code
YM = Date Code Marking
Y = Year (ex: V = 2008)
M = Month (ex: 9 = September)

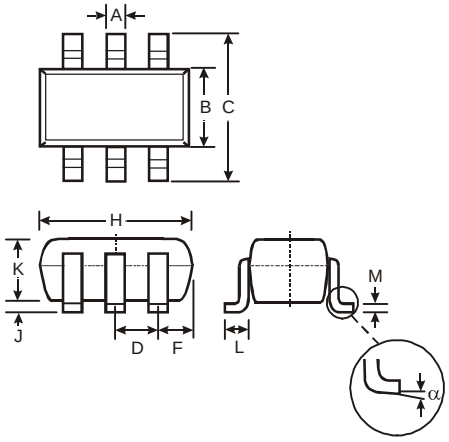
Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions

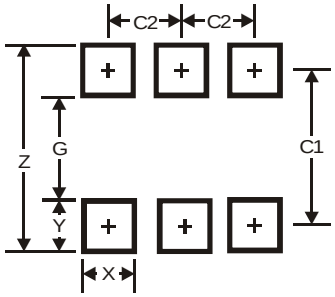
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT-363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Typ	
F	0.40	0.45
H	1.80	2.20
J	0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.22
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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